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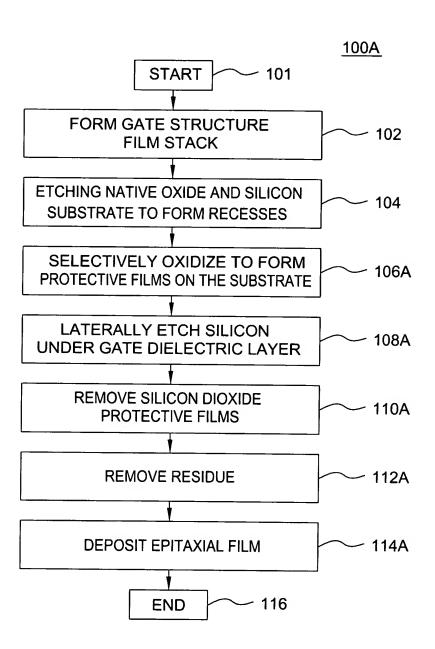


FIG. 1A

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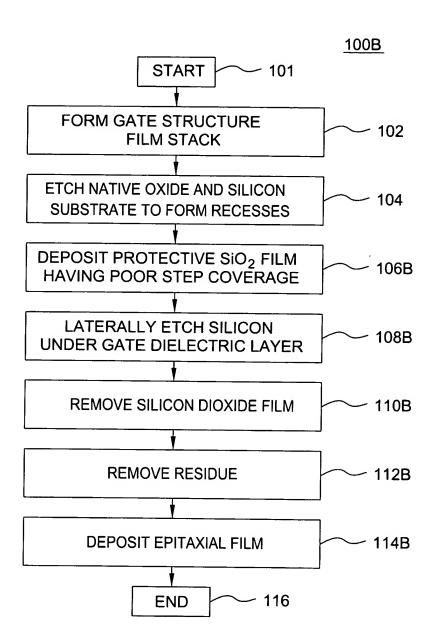


FIG. 1B

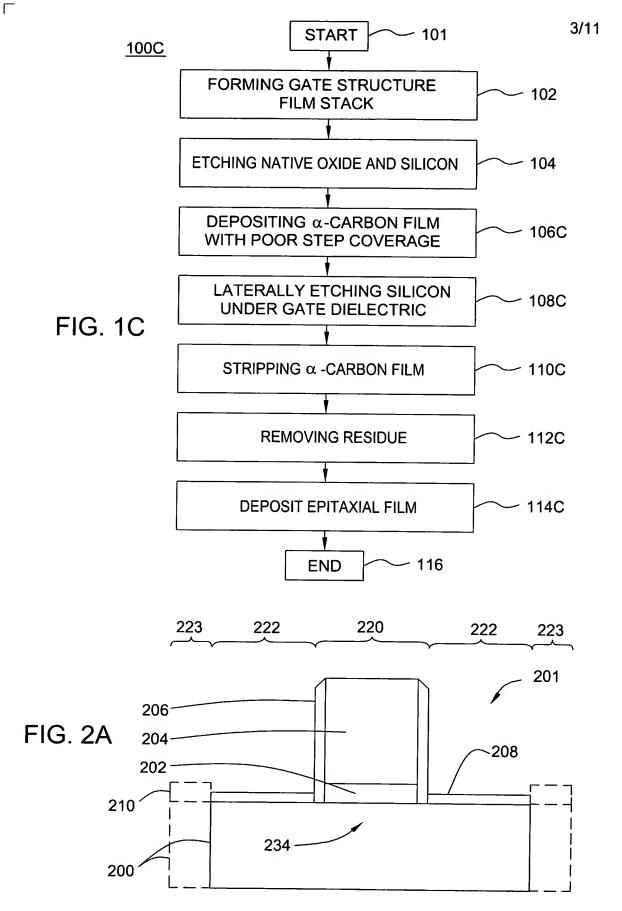
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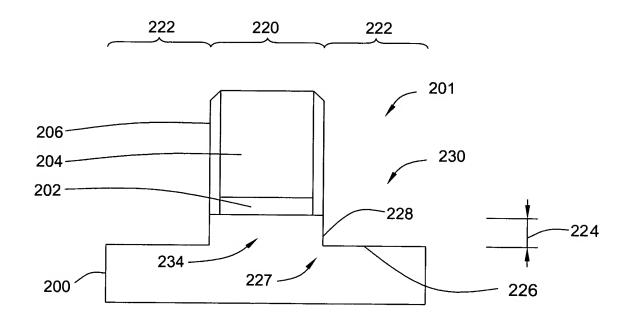


FIG. 2B

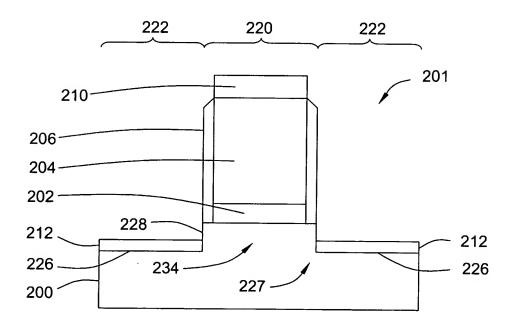


FIG. 2C

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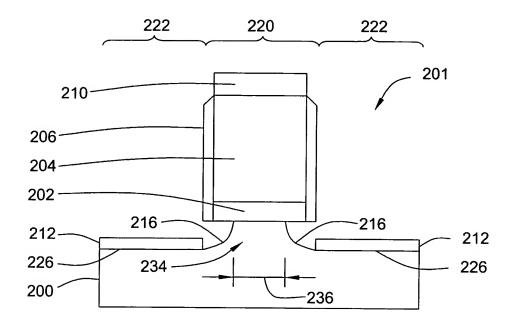


FIG. 2D

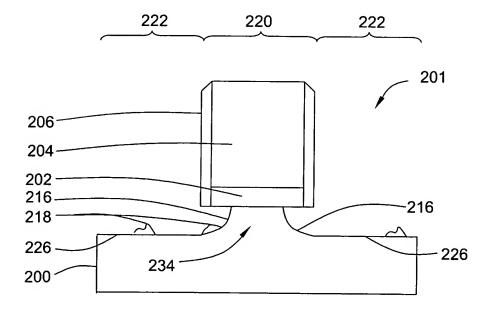


FIG. 2E

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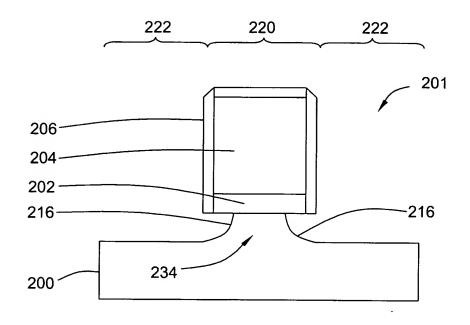


FIG. 2F

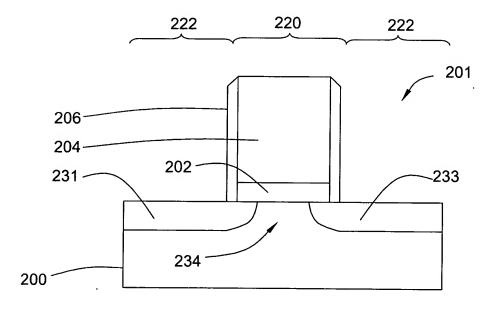


FIG. 2G

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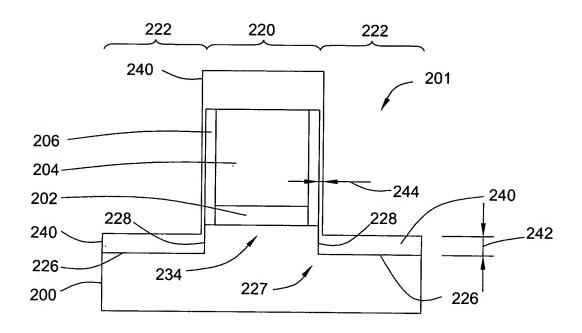


FIG. 2H

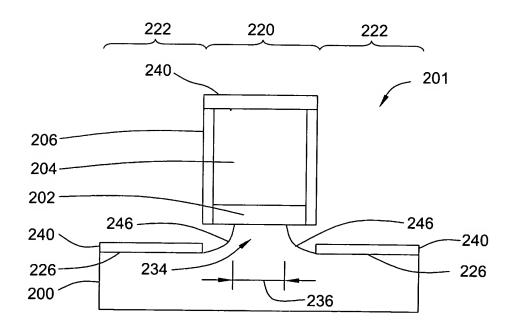


FIG. 21

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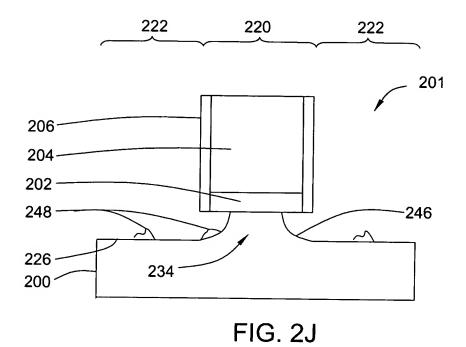
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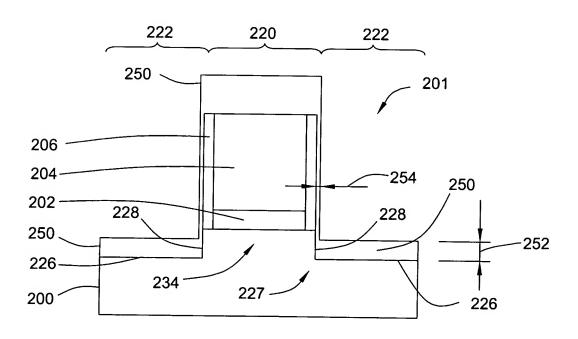


FIG. 2K

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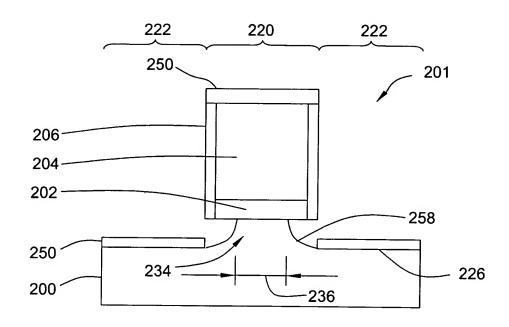


FIG. 2L

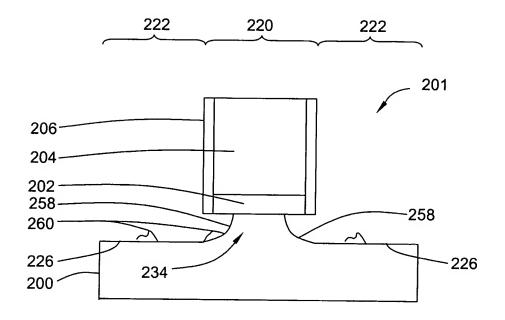


FIG. 2M

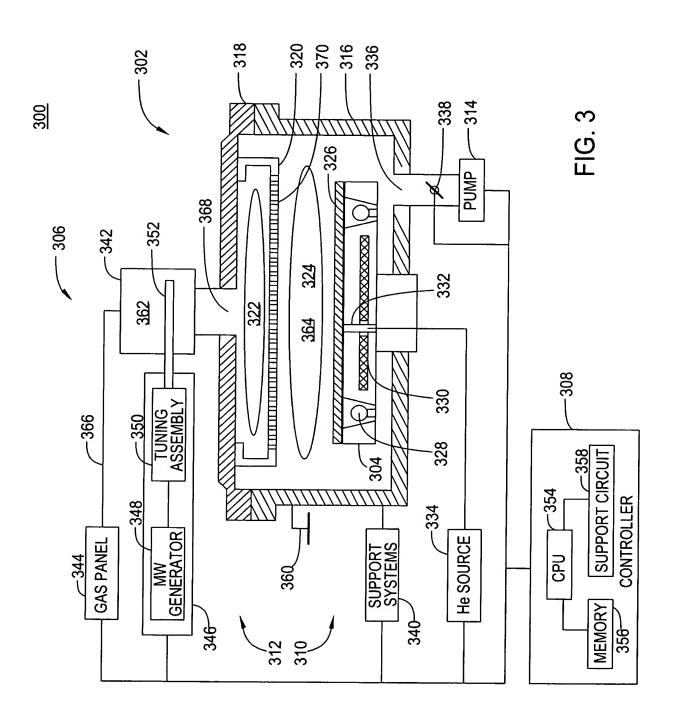
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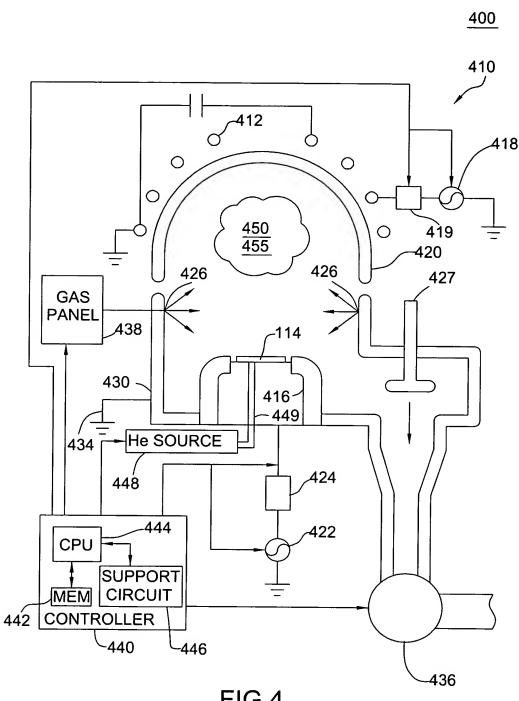


FIG.4